

Characteristics

Emitter (IR GaAs)	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Forward Voltage	V_F		1.25	1.65	V	$I_F=60\text{ mA}$
Reverse Current	I_R		0.01	10	μA	$V_R=6\text{ V}$
Capacitance	C_0		25		pF	$V_R=0\text{ V}, f=1\text{ MHz}$
Thermal Resistance, Junction to Lead	R_{THJL}		750		$^{\circ}\text{C/W}$	
Detector						
Collector-Emitter Leakage Current	I_{CEO}		5	70	nA	$V_{CE}=15\text{ V}$
Capacitance	C_{CE}		6.8		pF	$V_{CE}=5\text{ V}, f=1\text{ MHz}$
Thermal Resistance, Junction to Lead	R_{THJL}		500		$^{\circ}\text{C/W}$	
Package Transfer Characteristics (Each Channel)						
Saturated Current Transfer Ratio, ILD/Q3-1	CTR_{SAT}	300			%	$I_F=1.6\text{ mA}, V_{CE}=0.4\text{ V}$
Saturated Current Transfer Ratio, ILD/Q3-2	CTR_{SAT}	100			%	$I_F=1.0\text{ mA}, V_{CE}=0.4\text{ V}$
Common Mode Rejection Output High	CMH		5000		$\text{V}/\mu\text{s}$	$V_{CM}=50\text{ V}_{P-P}, R_L=10\text{ k}\Omega, I_F=0\text{ mA}$
Common Mode Rejection Output Low	CML		5000		$\text{V}/\mu\text{s}$	$V_{CM}=50\text{ V}_{P-P}, R_L=10\text{ k}\Omega, I_F=0\text{ mA}$
Common Mode Coupling Capacitance	C_{CM}		0.01		pF	
Package Capacitance	C_{IO}		0.8		pF	$V_{IO}=0\text{ V}, f=1\text{ MHz}$